



# SPP4953

## P-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPP4953 is the Dual P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application , notebook computer power management and other battery powered circuits where high-side switching .

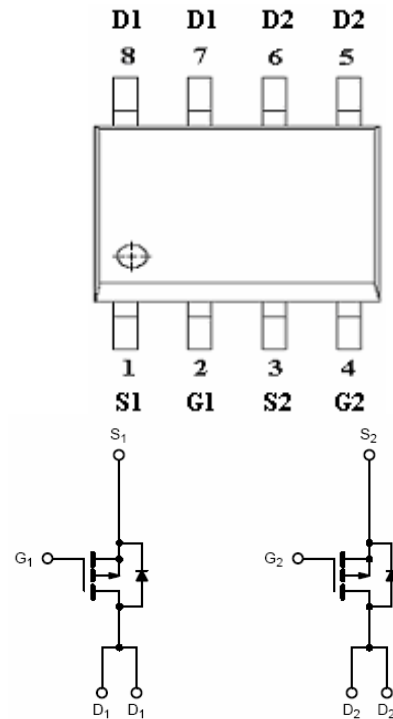
### FEATURES

- ◆ -30V/-5.0A, $R_{DS(ON)}= 60m\Omega@V_{GS}=- 10V$
- ◆ -30V/-4.5A, $R_{DS(ON)}= 80m\Omega@V_{GS}=- 6V$
- ◆ -30V/-3.7A, $R_{DS(ON)}= 90m\Omega@V_{GS}=-4.5V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOP – 8P package design

### APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

### PIN CONFIGURATION(SOP – 8P)



### PART MARKING





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### PIN DESCRIPTION

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	S2	Source 2
4	G2	Gate 2
5	D2	Drain 2
6	D2	Drain 2
7	D1	Drain 1
8	D1	Drain 1

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPP4953S8RG	SOP- 8P	SPP4953
SPP4953S8TG	SOP- 8P	SPP4953

※ SPP4953S8RG : 13" Tape Reel ; Pb – Free

※ SPP4953S8TG : Tube ; Pb – Free

### ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	-30	V	
Gate –Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	TA=25°C	-6.2	A
		TA=70°C	-4.0	
Pulsed Drain Current	I <sub>DM</sub>	-30	A	
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	-2.3	A	
Power Dissipation	P <sub>D</sub>	TA=25°C	2.8	W
		TA=70°C	1.8	
Operating Junction Temperature	T <sub>J</sub>	-55/150	°C	
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C	
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	70	°C/W	



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### ELECTRICAL CHARACTERISTICS

(T<sub>A</sub>=25°C Unless otherwise noted)

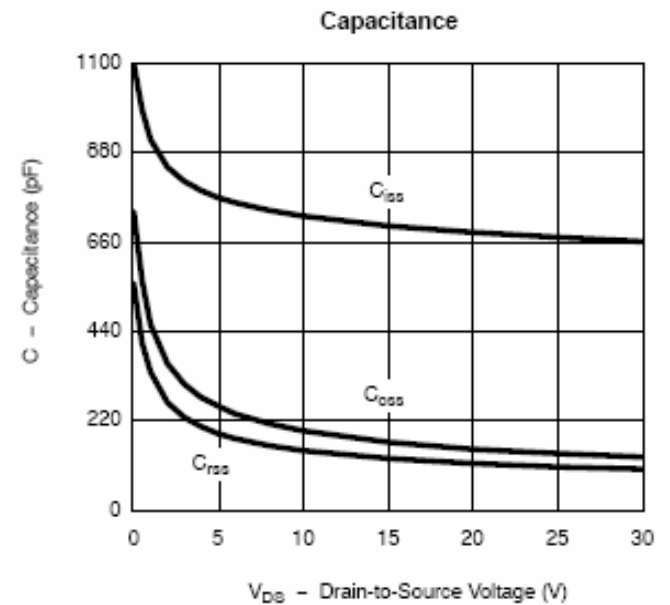
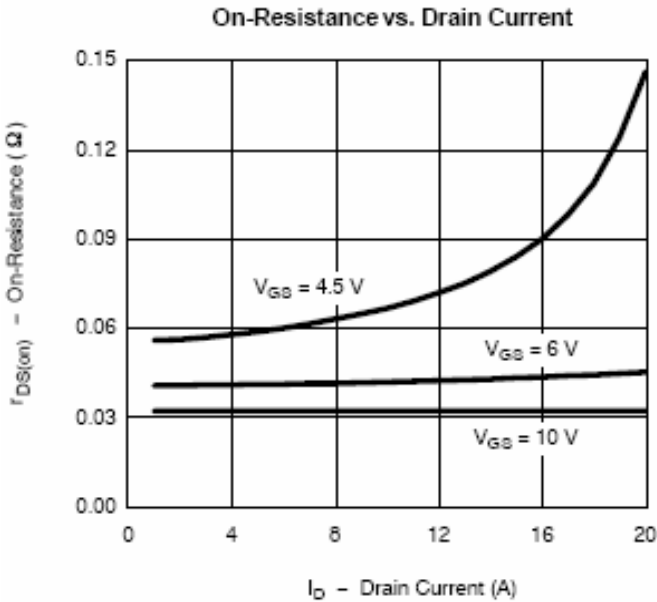
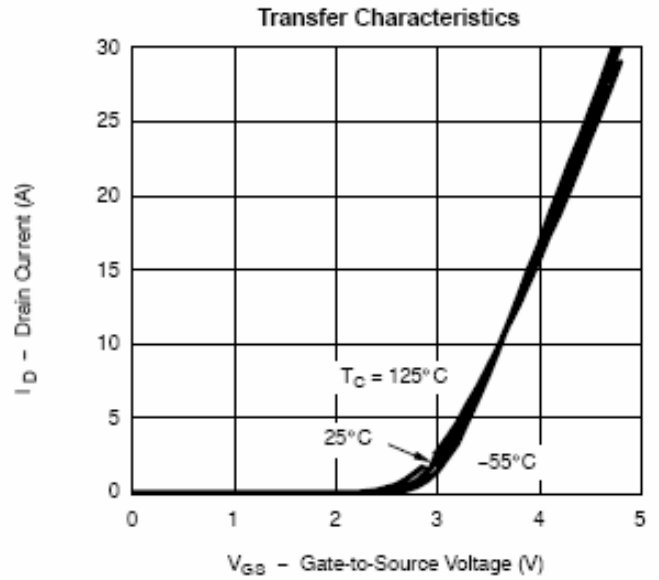
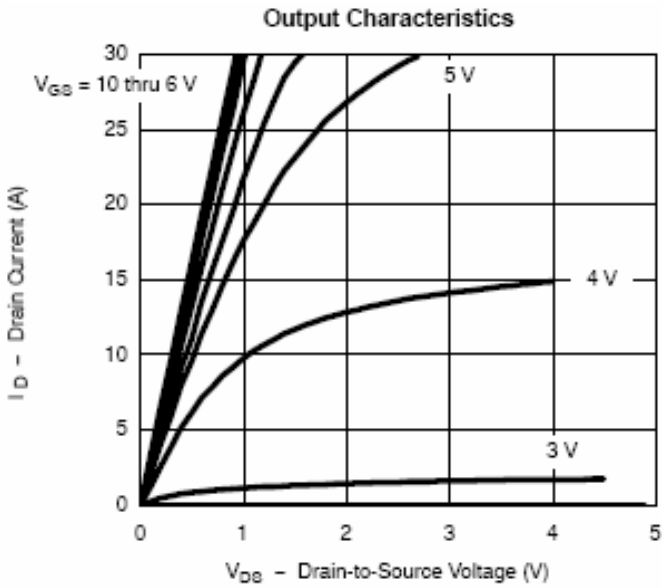
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1.0		-3.0	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V			-1	uA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			-5	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> = -5V, V <sub>GS</sub> =-10V	-25			A
Drain-Source On-Resistance	R <sub>DSS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.4A		0.050	0.060	Ω
		V <sub>GS</sub> =-6.0V, I <sub>D</sub> =-4.6A		0.060	0.080	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.0A		0.075	0.090	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-5.0A		9		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-2.0A, V <sub>GS</sub> =0V		-0.8	-1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V I <sub>D</sub> = -5.0A		15	25	nC
Gate-Source Charge	Q <sub>gs</sub>			4		
Gate-Drain Charge	Q <sub>gd</sub>			2		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V f=1MHz		680		pF
Output Capacitance	C <sub>oss</sub>			120		
Reverse Transfer Capacitance	C <sub>rss</sub>			75		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, R <sub>L</sub> =15Ω I <sub>D</sub> =-1.0A, V <sub>GEN</sub> =-10V R <sub>G</sub> =6Ω		7	15	nS
	t <sub>r</sub>			10	20	
Turn-Off Time	t <sub>d(off)</sub>			40	80	
	t <sub>f</sub>			20	40	



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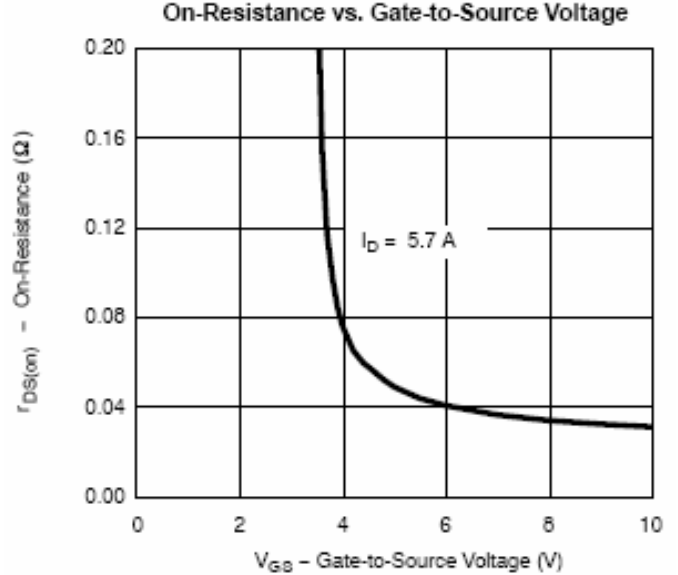
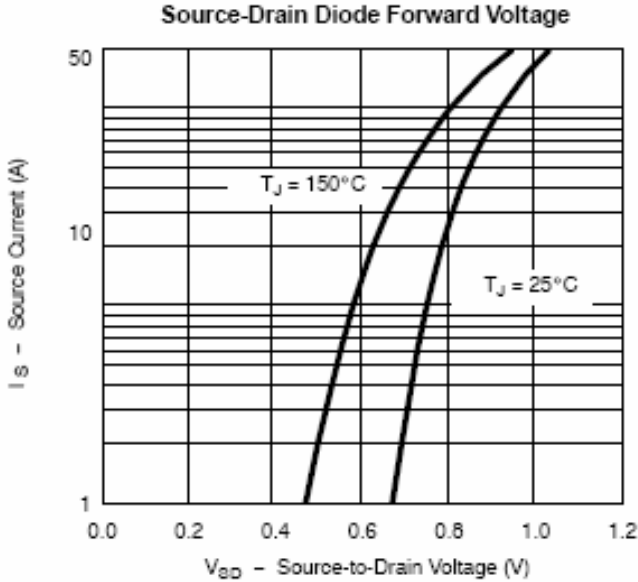
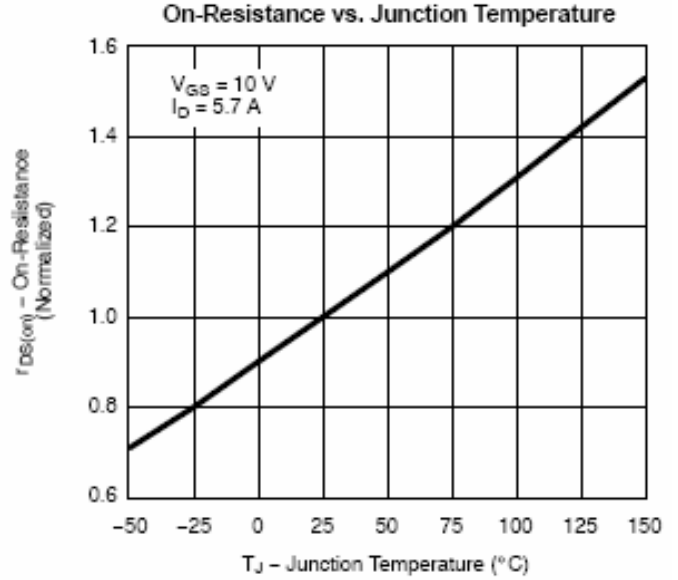
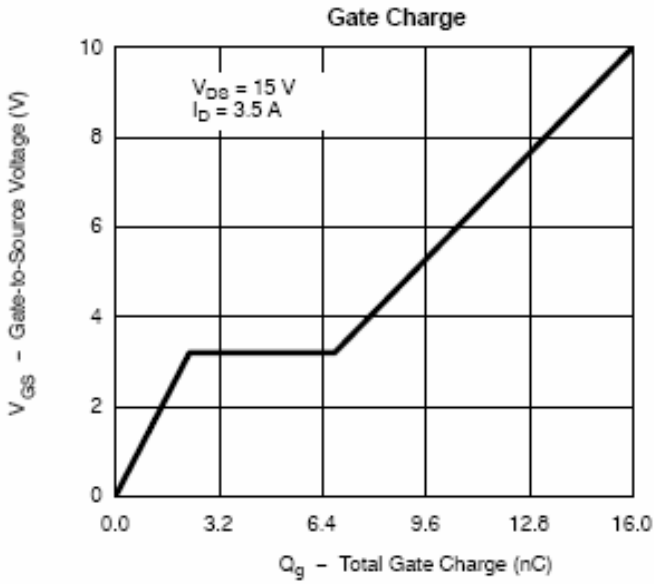
### TYPICAL CHARACTERISTICS





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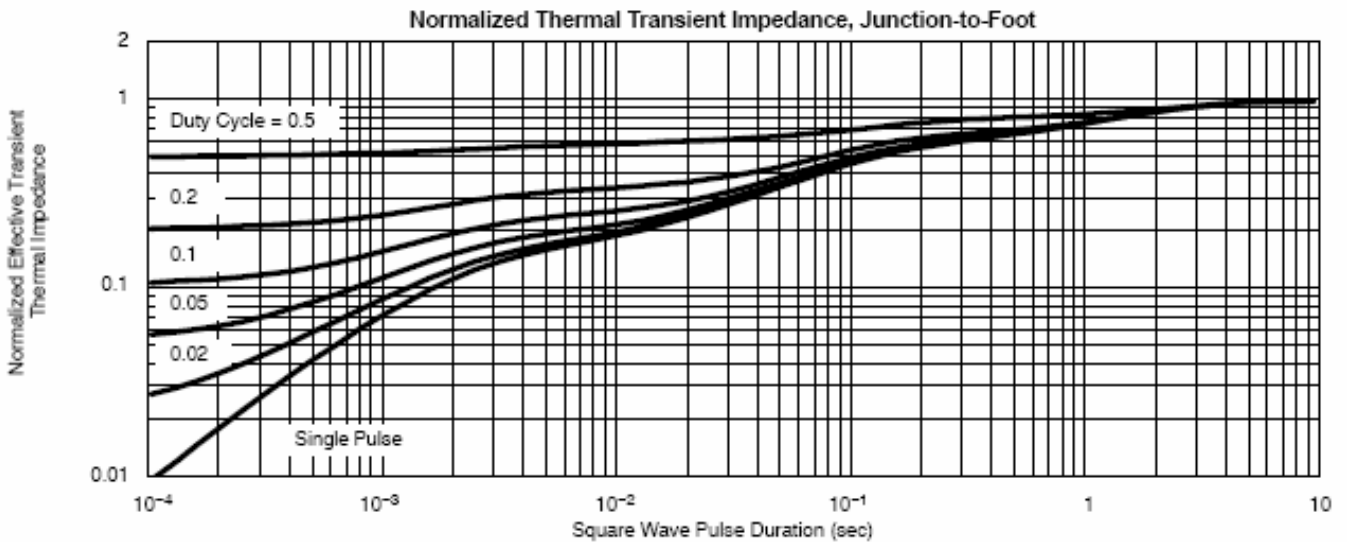
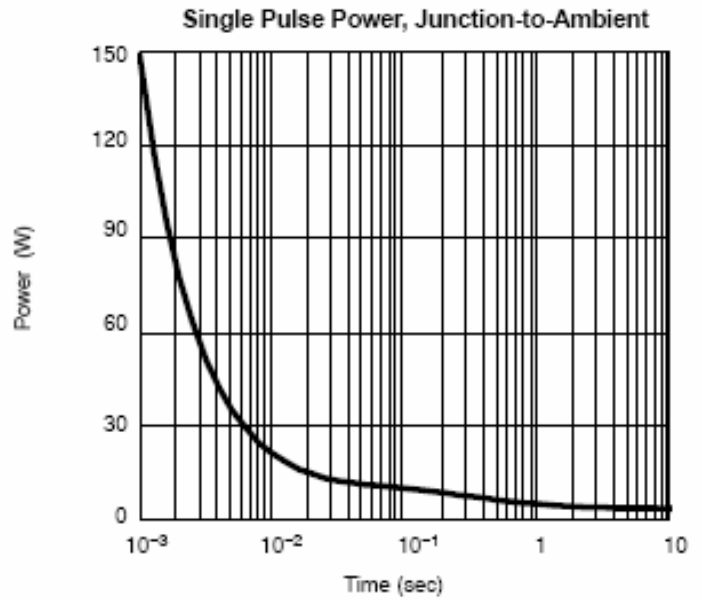
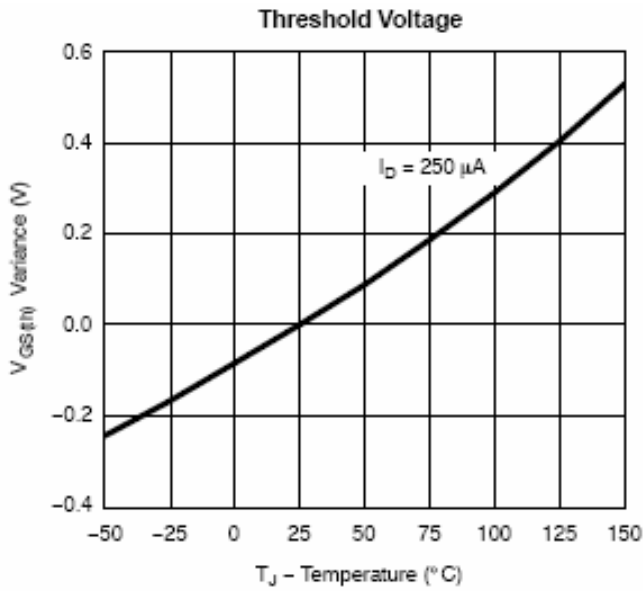
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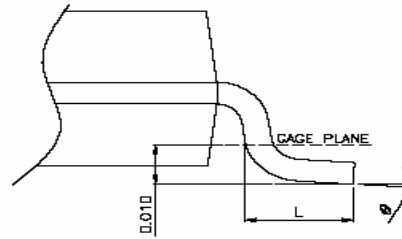
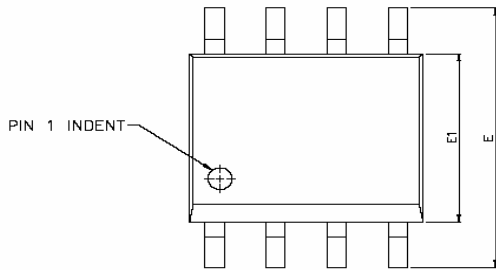
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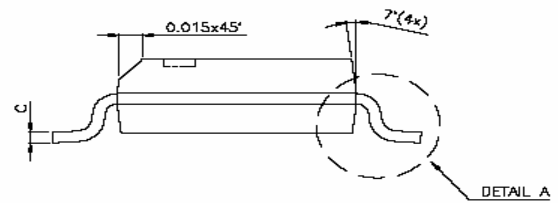
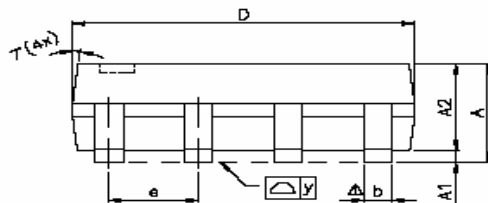


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## SOP- 8 PACKAGE OUTLINE



DETAIL A



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	—	0.25	0.004	—	0.010
A2	—	1.45	—	—	0.057	—
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	—	1.27	—	—	0.050	—
L	0.38	0.71	1.27	0.015	0.028	0.050
$\Delta$ y	—	—	0.076	—	—	0.003
$\theta$	0°	—	8°	0°	—	8°



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